

Super FAP-G Series**N-CHANNEL SILICON POWER MOSFET****■ Features**

High speed switching
Low on-resistance
No secondary breakdown
Low driving power
Avalanche-proof

■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

■ Maximum ratings and characteristic Absolute maximum ratings**● (Tc=25°C unless otherwise specified)**

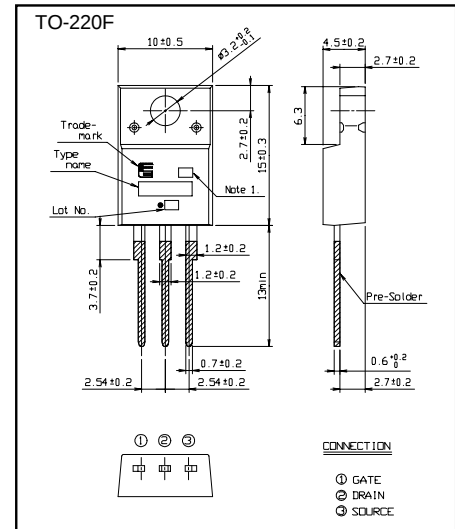
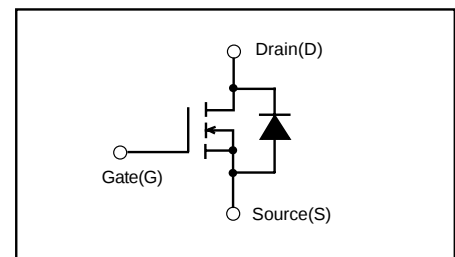
Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	500	V
Continuous drain current	I _D	±16	A
Pulsed drain current	I _D (puls)	±64	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	IAR *2	16	A
Maximum Avalanche Energy	EAS*1	183	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt *4	20	kV/μs
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs
Max. power dissipation	P _D	Ta=25°C	2.16
		Tc=25°C	80
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C
Isolation Voltage	V _{ISO} *5	2	kVrms

*1 L=1.53mH, V_{CC}=50V, See to Avalanche Energy Graph *2 T_{ch}≤150°C*3 I_F≤-I_D, -di/dt=50A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C *4 V_{DS}≤500V *5 t=60sec, f=60Hz**● Electrical characteristics (Tc=25°C unless otherwise specified)**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V(BR) _{DSS}	I _D =250μA V _{GS} =0V	500			V
Gate threshold voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =500V V _{GS} =0V T _{ch} =25°C			25	μA
		V _{DS} =400V V _{GS} =0V T _{ch} =125°C			250	μA
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =7A V _{GS} =10V		0.35	0.46	Ω
Forward transconductance	g _{fs}	I _D =7A V _{DS} =25V	7	14		S
Input capacitance	C _{iss}	V _{DS} =25V		1600	2400	pF
Output capacitance	C _{oss}	V _{GS} =0V		160	240	pF
Reverse transfer capacitance	C _{rss}	f=1MHz		7	10.5	pF
Turn-on time t _{on}	td(on)	V _{CC} =300V I _D =7A		18	27	ns
	t _r	V _{GS} =10V		16	24	ns
Turn-off time t _{off}	td(off)	R _{GS} =10 Ω		35	50	ns
	t _f			8	15	ns
Total Gate Charge	Q _G	V _{CC} =250V		33	50	nC
Gate-Source Charge	Q _{GS}	I _D =14A		12.5	19	nC
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		10.5	16	nC
Avalanche capability	I _{AV}	L=1.53mH T _{ch} =25°C	16			A
Diode forward on-voltage	V _{SD}	I _F =14A V _{GS} =0V T _{ch} =25°C		1.00	1.50	V
Reverse recovery time	t _{rr}	I _F =14A V _{GS} =0V		0.65		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		6.0		μC

● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			1.56	°C/W
	R _{th(ch-a)}	channel to ambient			62.0	°C/W

■ Outline Drawings [mm]**■ Equivalent circuit schematic**

Characteristics

